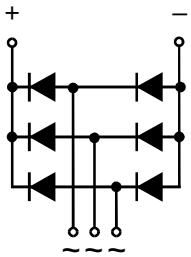
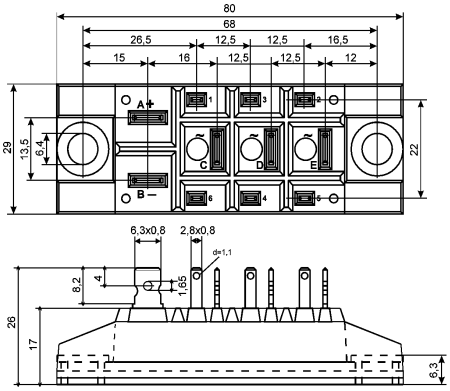
S3PDB30

Three Phase Rectifier Modules



Type	V_{RSM} V	V_{RRM} V
S3PDB30N08	900	800
S3PDB30N12	1300	1200
S3PDB30N14	1500	1400
S3PDB30N16	1700	1600
S3PDB30N18	1900	1800

Dimensions in mm (1mm=0.0394")



Symbol	Test Conditions		Maximum Ratings	Unit
I_{dav}	T_C=100°C, module		30	A
I_{FSM}	T_{VJ}=45°C V_R=0	t=10ms (50Hz), sine t=8.3ms (60Hz), sine	270 300	A
	T_{VJ}=T_{VJM} V_R=0	t=10ms(50Hz), sine t=8.3ms(60Hz), sine	230 255	
I^2t	T_{VJ}=45°C V_R=0	t=10ms (50Hz), sine t=8.3ms (60Hz), sine	450 460	A^2s
	T_{VJ}=T_{VJM} V_R=0	t=10ms(50Hz), sine t=8.3ms(60Hz), sine	350 360	
T_{VJ} T_{VJM} T_{stg}			-40...+150 150 -40...+125	°C
V_{ISOL}	50/60Hz, RMS I_{ISOL}≤1mA	t=1min t=1s	2500 3000	V~
M_d	Mounting torque (M6)		4.7	Nm
Weight	typ.		50	g

Sirectifier®

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Symbol	Test Conditions	Characteristic Values	Unit
I_R	$V_R=V_{RRM}$; $T_{VJ}=25^oC$ $V_R=V_{RRM}$; $T_{VJ}=T_{VJM}$	≤ 0.3 ≤ 5	mA
V_F	I_F=10A; $T_{VJ}=25^oC$	1.2	V
V_{TO}	For power-loss calculations only	0.8	V
r_T		40	mΩ
R_{thJC}	per diode per module	0.9 0.15	K/W
R_{thJK}	per diode per module	1.1 0.57	K/W
d_S	Creeping distance on surface	16.1	mm
d_A	Creepage distance in air	7.5	mm
a	Max. allowable acceleration	50	m/s^2

FEATURES
* Package with copper base plate
* Isolation voltage 3000 V~
* Planar passivated chips
* 1/4" fast-on power terminal
* Low forward voltage drop

APPLICATIONS
* Supplies for DC power equipment
* Input rectifiers for PWM inverter
* Battery DC power supplies
* Field supply for DC motors

ADVANTAGES
* Easy to mount with two screws
* Space and weight savings
* Improved temperature and power cycling

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